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November 2013



## FGA20N120FTD 1200 V, 20 A Field Stop Trench IGBT

## Features

- Field Stop Trench Technology
- High Speed Switching
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.6 V @ I<sub>C</sub> = 20 A
- High Input Impedance
- RoHS Compliant

## Applications

Induction Heating, Microvewave Oven

## **General Description**

Using advanced field stop trench technology, Fairchild's 1200V trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche ruggedness. This device is designed for induction heating and microwave oven.



## **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		1200	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 25	V
I <sub>C</sub>	Continuous Collector Current	@ T <sub>C</sub> = 25 <sup>o</sup> C	40	A
	Continuous Collector Current	@ T <sub>C</sub> = 100°C	20	A
I <sub>CM (1)</sub>	Pulsed Collector Current		60	А
I <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 25 <sup>o</sup> C	20	А
	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	10	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	298	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	119	W
Т <sub>Ј</sub>	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:

1: Repetitive rating, Pulse width limited by max. junction temperature

## **Thermal Characteristics**

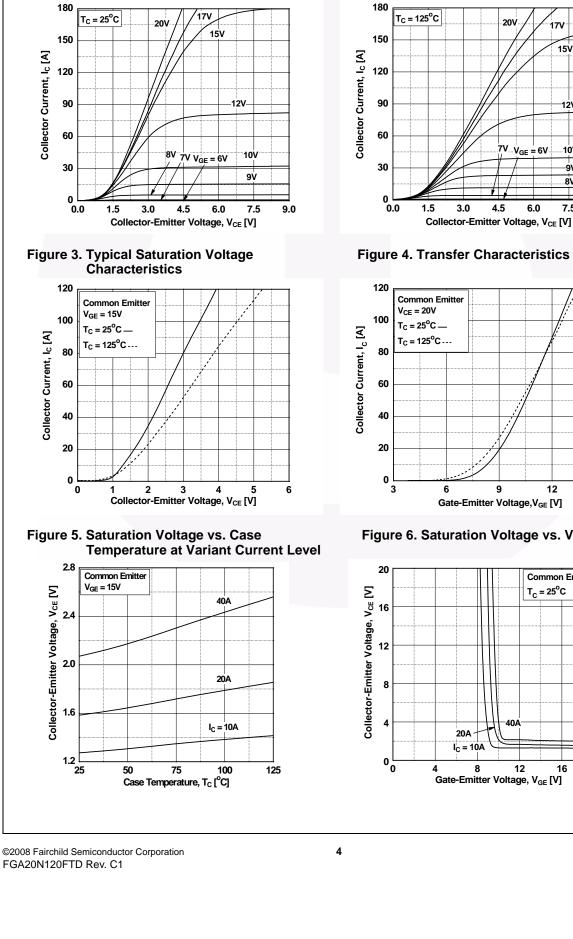
Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.42	°C/W
R <sub>0JC</sub> (Diode) Thermal Resistance, Junction to Case		-	2.0	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Part NumberTop MarkPackageFGA20N120FTDTUFGA20N120FTDTO-3P		Package	Packing Method	Reel Size	Tape Width		Quantity	
		Tube	N/A	N/A		30		
Electric	al Cha	racteristics	of the IG	<b>BT</b> T <sub>C</sub> = 25°C unless otherw	ise noted			
Symbol		Parameter		Test Condition	s Min.	Тур.	Мах	. Unit
Off Charac	teristics							
BV <sub>CES</sub>	Collector	to Emitter Breakdo	wn Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA	1200	-	-	V
ICES		r Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current			$V_{GE} = V_{GES}, V_{CE} = 0 V$ -		-	±250	) nA
On Charac	toristics	-						
V <sub>GE(th)</sub>	r	eshold Voltage		I <sub>C</sub> = 20 mA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	5.9	7.5	V
V <sub>CE(sat)</sub>		Collector to Emitter Saturation Voltage		$I_{C} = 20 \text{ A}, V_{GE} = 15 \text{ V}$ $I_{C} = 25^{\circ}\text{C}$	-	1.59	2	V
02(00)				$I_{C} = 20 \text{ A}, V_{GE} = 15 \text{ V},$ $T_{C} = 125^{\circ}\text{C}$	-	1.85	-	v
Dynamic C	haracteri	stics	·					·
C <sub>ies</sub>	r	pacitance			-	3080	-	pF
C <sub>oes</sub>	Output C	Capacitance		$V_{CE} = 30 V, V_{GE} = 0 V,$	-	95	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance		f = 1 MHz	-	60	-	pF	
Switching	Character	ristics						
t <sub>d(on)</sub>	Turn-On Delay Time Rise Time				-	30	-	ns
t <sub>r</sub>				-	79	-	ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time		V <sub>CC</sub> = 600 V, I <sub>C</sub> = 20 A,	-	143	-	ns
t <sub>f</sub>	Fall Time			$R_{G} = 10 \Omega$ , $V_{GE} = 15 V$ ,	-	217	320	ns
E <sub>on</sub>	Turn-On	Switching Loss		Resistive Load, $T_C = 25^{\circ}C$	-	0.42	-	mJ
E <sub>off</sub>	Turn-Off	Switching Loss			-	0.71	1.05	mJ
E <sub>ts</sub>	Total Sw	itching Loss			-	1.13	-	mJ
t <sub>d(on)</sub>	Turn-On	Delay Time			-	29	-	ns
t <sub>r</sub>	Rise Tim	e			-	93	-	ns
t <sub>d(off)</sub>	Turn-Off	Delay Time		V <sub>CC</sub> = 600 V, I <sub>C</sub> = 20 A,	-	147	-	ns
t <sub>f</sub>	Fall Time	9		R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,		259	-	ns
Eon	Turn-On	Switching Loss		Resistive Load, T <sub>C</sub> = 125 <sup>c</sup>	-	0.47	-	mJ
E <sub>off</sub>	Turn-Off	Switching Loss			-	0.86	-	mJ
E <sub>ts</sub>	Total Sw	itching Loss			-	1.33	-	mJ
Qg	Total Gat	te Charge			-	137	-	nC
Q <sub>ge</sub>	Gate to I	Emitter Charge		$V_{CE} = 600 \text{ V}, I_{C} = 20 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	23	-	nC
Q <sub>gc</sub>	Gate to 0	Collector Charge		- GE - 10 V	-	65	-	nC

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Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V	FM Diode Forward Voltage	I <sub>F</sub> = 20 A	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	1.3	1.7	V
* FIM			T <sub>C</sub> = 125°C	-	1.3	-	
t <sub>rr</sub>	Diode Reverse Recovery Time	- I <sub>F</sub> =20 A, di <sub>F</sub> /dt = 200 A/μs	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	447	-	ns
•rr			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	485	-	
l	Diode Peak Reverse Recovery Current		$T_{C} = 25^{\circ}C$	-	48	-	А
'rr			$T_{\rm C} = 125^{\rm o}{\rm C}$	•	50	-	
Q <sub>rr</sub> [	Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\rm o}{\rm C}$	-	10.8	-	μC
			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	12	-	μΟ

FGA20N120FTD — 1200 V, 20 A Field Stop Trench IGBT



### **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

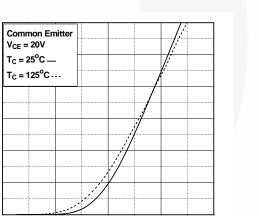


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

9

Gate-Emitter Voltage, V<sub>GE</sub> [V]

12

15

6

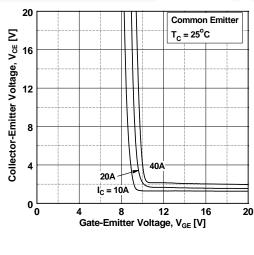


Figure 2. Typical Output Characteristics

3.0

4.5

20\

V\_V\_V\_GE = 6V

6.0

17V

15V

12V

..10V

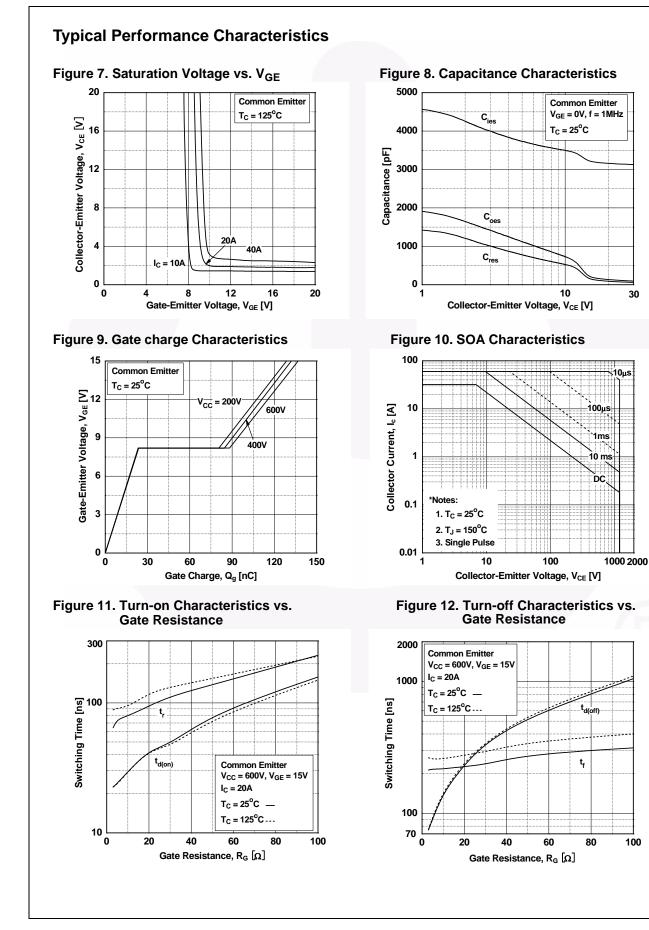
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8V.

7.5

9.0

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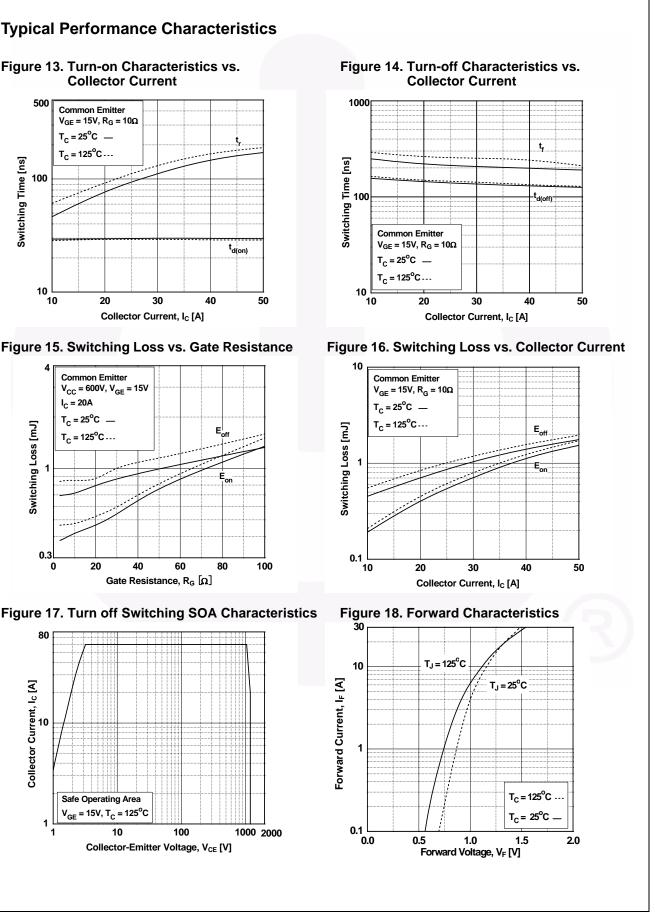


Figure 15. Switching Loss vs. Gate Resistance

30

**Collector Current** 

Common Emitter  $V_{GE} = 15V, R_G = 10\Omega$  $T_{c} = 25^{\circ}C$  —

T<sub>C</sub> = 125<sup>o</sup>C ....

20

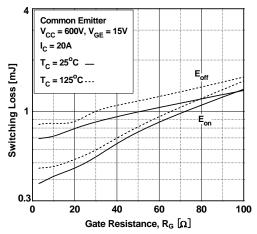
500

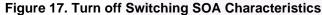
100

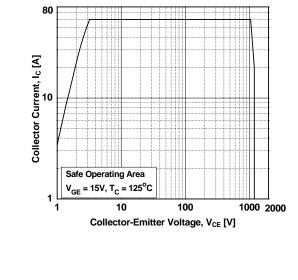
10

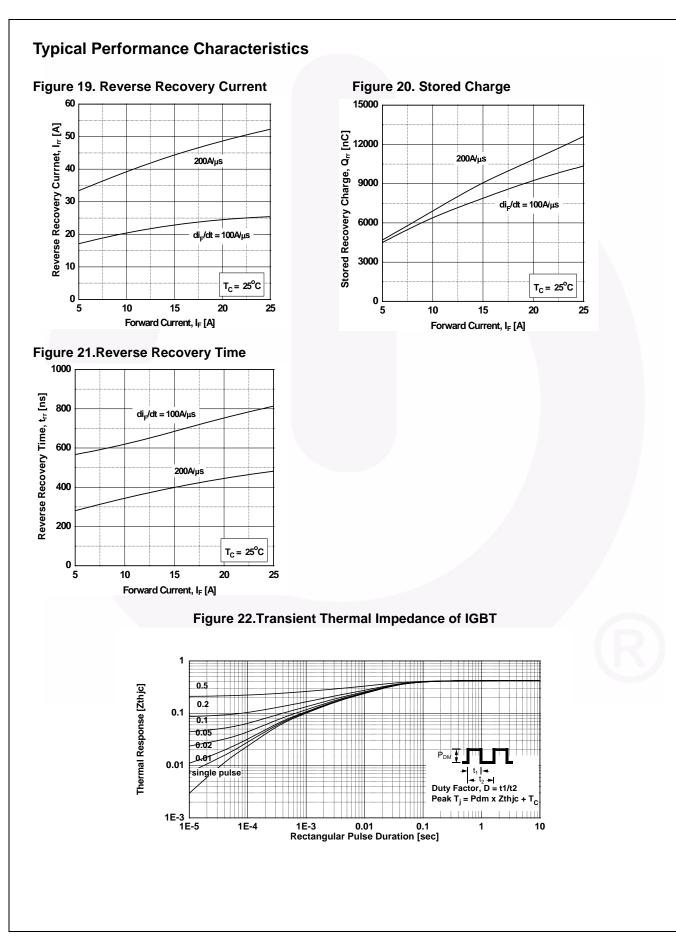
10

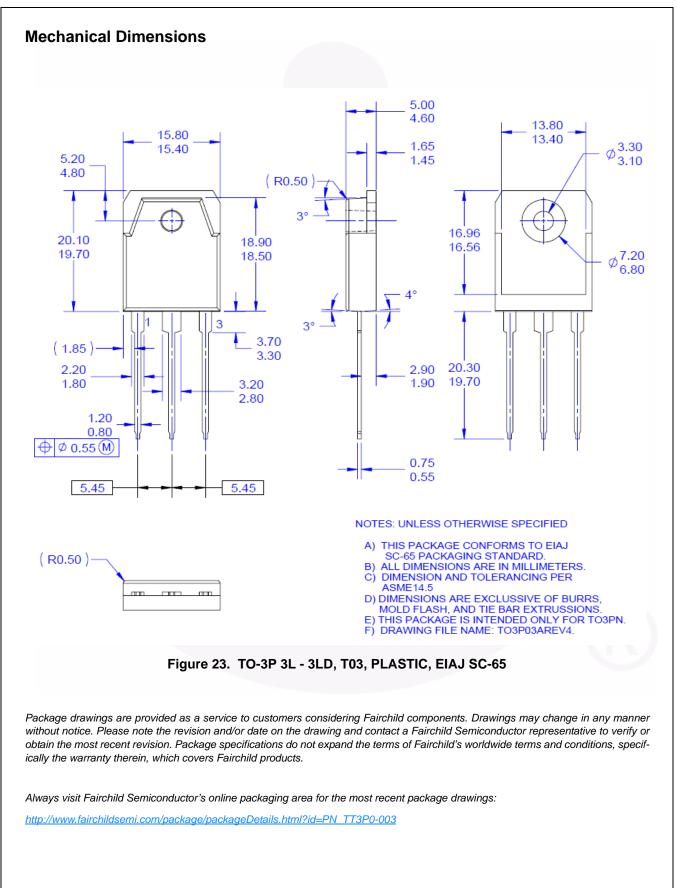
Switching Time [ns]











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